

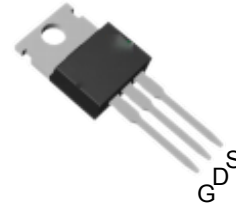
Features

- 60V/110A,
 $R_{DS(ON)} = 6m\Omega$ (typ.) @ $V_{GS} = 10V$
- 100% UIS + R_g Tested
- Reliable and Rugged
- Lead Free and Green Devices Available
(RoHS Compliant)

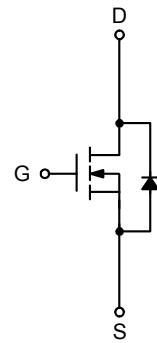
Applications

- Synchronous Rectification.
- Power Management in Inverter Systems.

Pin Description



Top View of TO-220



N-Channel MOSFET

Absolute Maximum Ratings ($T_A = 25^\circ\text{C}$ Unless Otherwise Noted)

Symbol	Parameter		Rating	Unit
Common Ratings				
V _{DSS}	Drain-Source Voltage		60	V
V _{GSS}	Gate-Source Voltage		±25	
T _J	Maximum Junction Temperature		175	°C
T _{STG}	Storage Temperature Range		-55 to 175	
I _S	Diode Continuous Forward Current	T _C =25°C	110	A
Mounted on Large Heat Sink				
I _{DP}	Pulse Drain Current Tested	T _C =25°C	330	A
I _D	Continuous Drain Current	T _C =25°C	110	A
		T _C =100°C	44	
P _D	Maximum Power Dissipation	T _C =25°C	150	W
		T _C =100°C	75	
R _{θJC}	Thermal Resistance-Junction to Case		1	°C/W
R _{θJA}	Thermal Resistance-Junction to Ambient		62.5	
I _{AS} ^b	Avalanche Current, Single pulse	L=0.5mH	45	A
E _{AS} ^b	Avalanche Energy, Single pulse	L=0.5mH	506	mJ

Note * : Bonding wire limitation current is 80A.

Note a : Pulse width limited by max. junction temperature.

Note b : UIS tested and pulse width limited by maximum junction temperature 150°C (initial temperature $T_J=25^\circ\text{C}$).

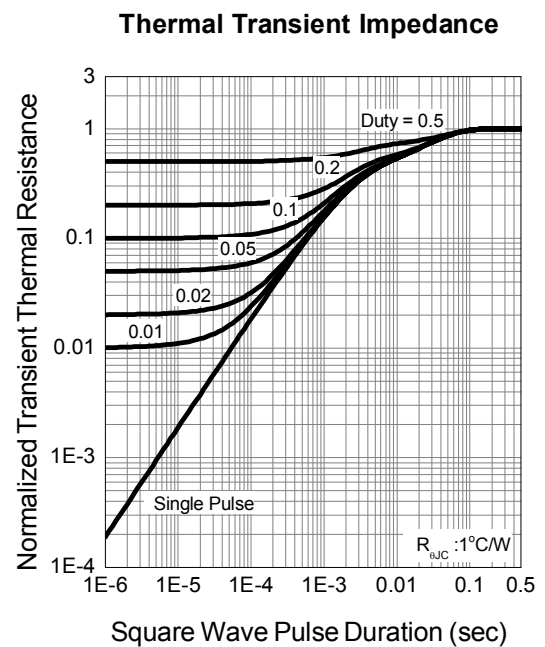
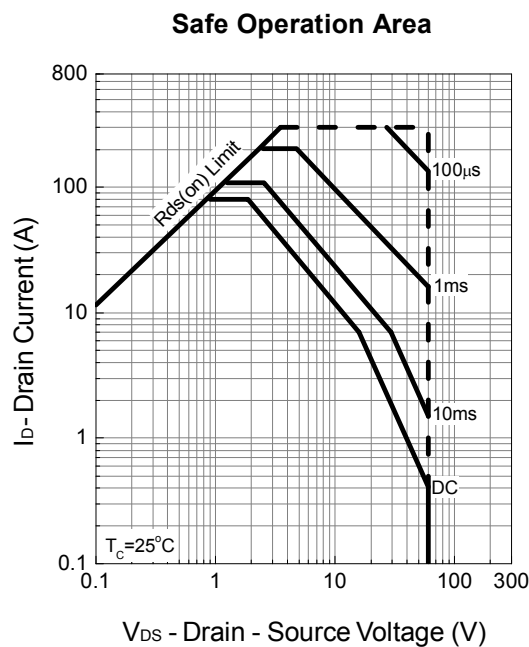
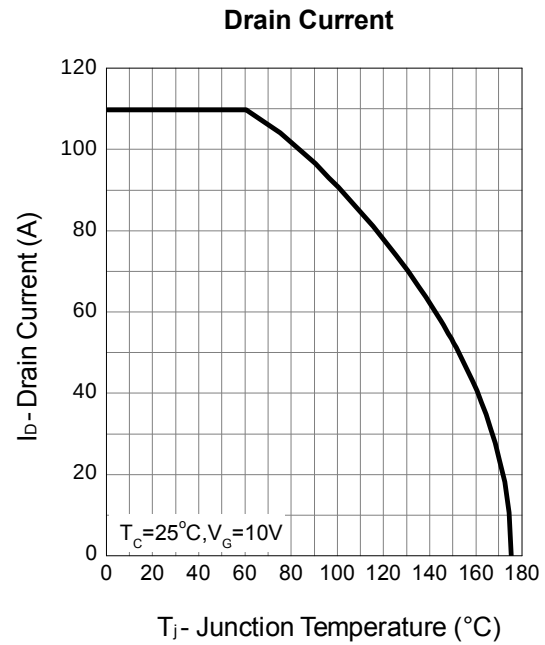
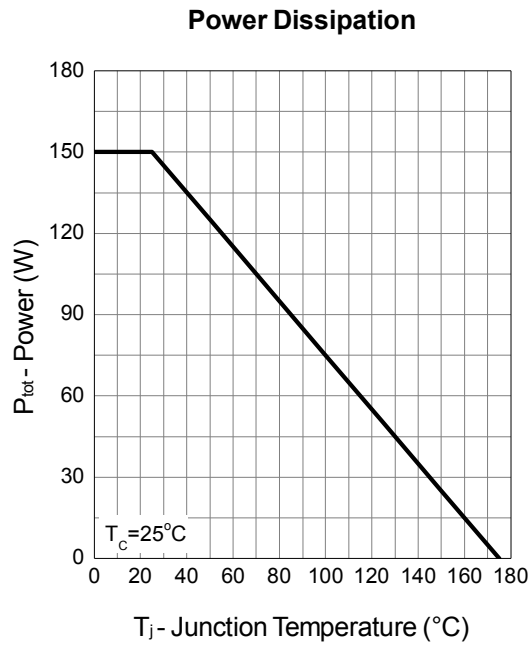
Electrical Characteristics (T_A = 25°C Unless Otherwise Noted)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
Static Characteristics						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _{DS} =250μA	60	-	-	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =48V, V _{GS} =0V T _J =85°C	-	-	1 30	μA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _{DS} =250μA	2	3	4	V
I _{GSS}	Gate Leakage Current	V _{GS} =±25V, V _{DS} =0V	-	-	±100	nA
R _{DS(ON)} ^c	Drain-Source On-state Resistance	V _{GS} =10V, I _{DS} =40A	-	6	8	mΩ
Diode Characteristics						
V _{SD} ^c	Diode Forward Voltage	I _{SD} =20A, V _{GS} =0V	-	0.8	1.3	V
t _{rr}	Reverse Recovery Time	I _{SD} =40A, dI _{SD} /dt=100A/μs	-	30	-	ns
Q _{rr}	Reverse Recovery Charge		-	32	-	nC
Dynamic Characteristics ^d						
R _G	Gate Resistance	V _{GS} =0V, V _{DS} =0V, f=1MHz	-	1	-	Ω
C _{iss}	Input Capacitance	V _{GS} =0V, V _{DS} =30V, Frequency=1.0MHz	-	4585	4960	pF
C _{oss}	Output Capacitance		-	385	-	
C _{rss}	Reverse Transfer Capacitance		-	355	-	
t _{d(ON)}	Turn-on Delay Time	V _{DD} =30V, R _L =30Ω, I _{DS} =1A, V _{GEN} =10V, R _G =6Ω	-	16	29	ns
t _r	Turn-on Rise Time		-	10	18	
t _{d(OFF)}	Turn-off Delay Time		-	40	72	
t _f	Turn-off Fall Time		-	35	63	
Gate Charge Characteristics ^d						
Q _g	Total Gate Charge	V _{DS} =30V, V _{GS} =10V, I _{DS} =40A	-	46	65	nC
Q _{gs}	Gate-Source Charge		-	16	-	
Q _{gd}	Gate-Drain Charge		-	12	-	

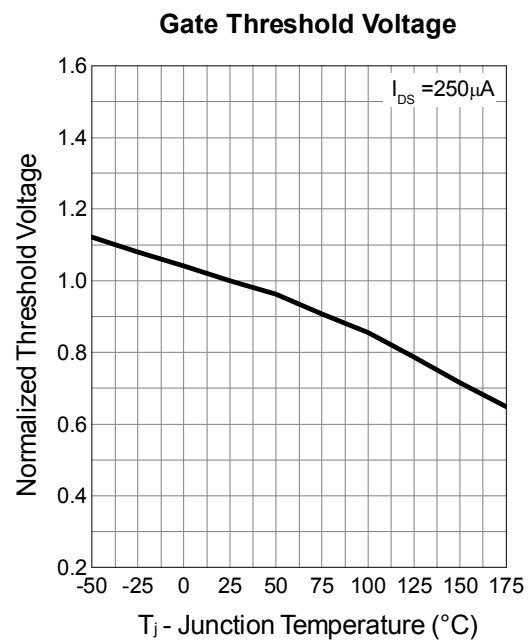
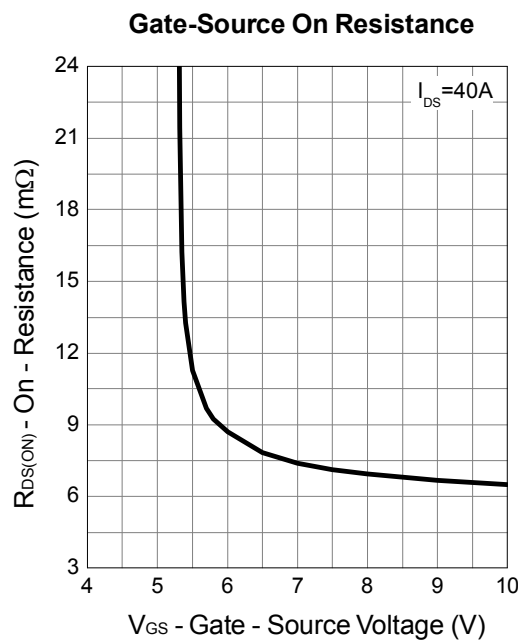
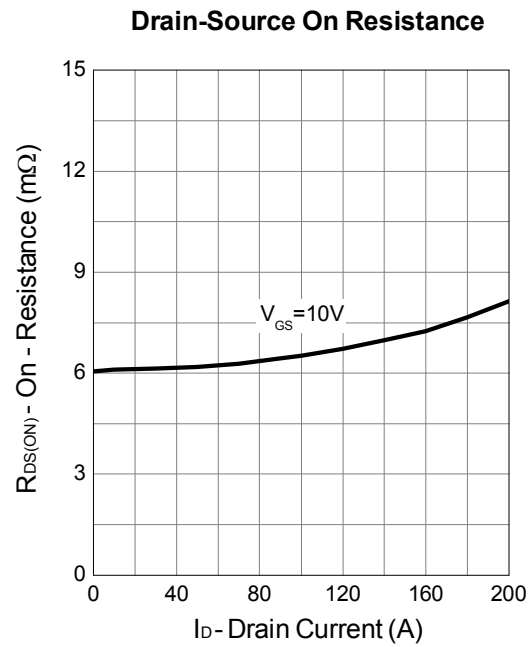
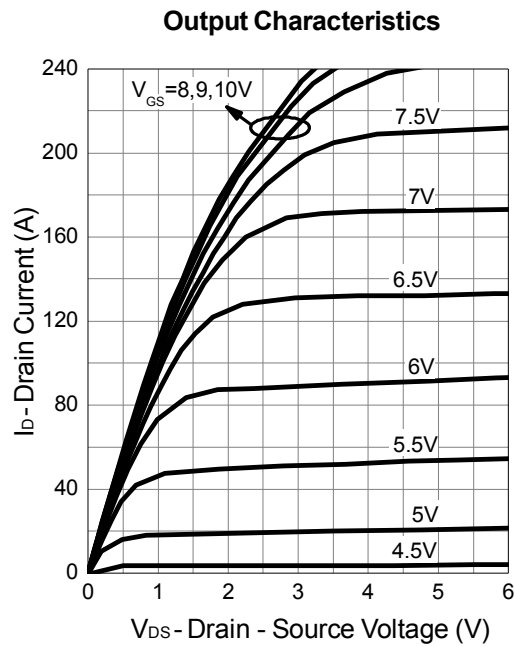
Note c : Pulse test ; pulse width≤300μs, duty cycle≤2%.

Note d : Guaranteed by design, not subject to production testing.

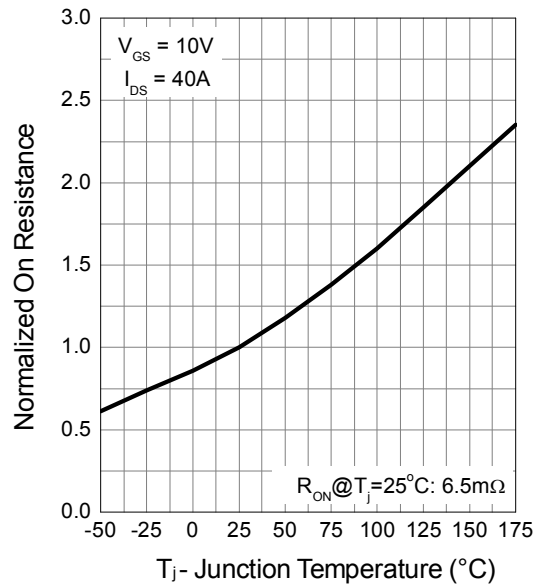
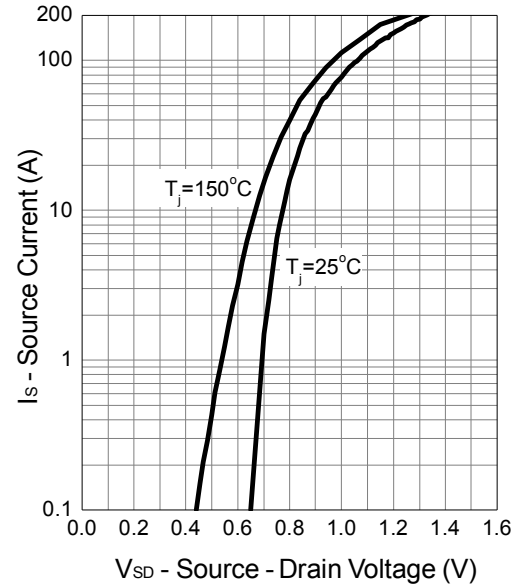
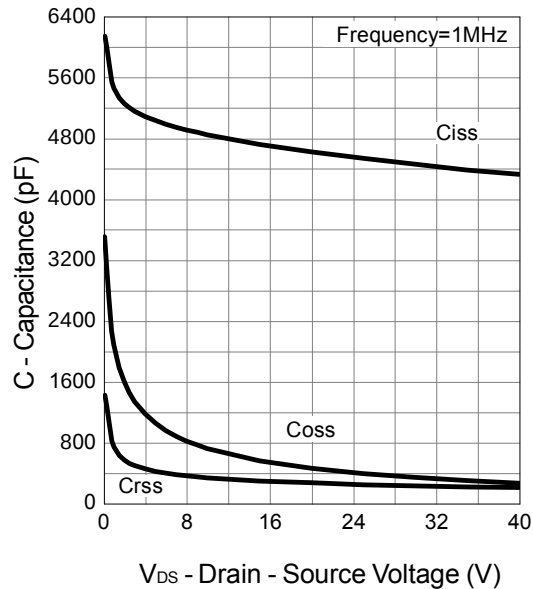
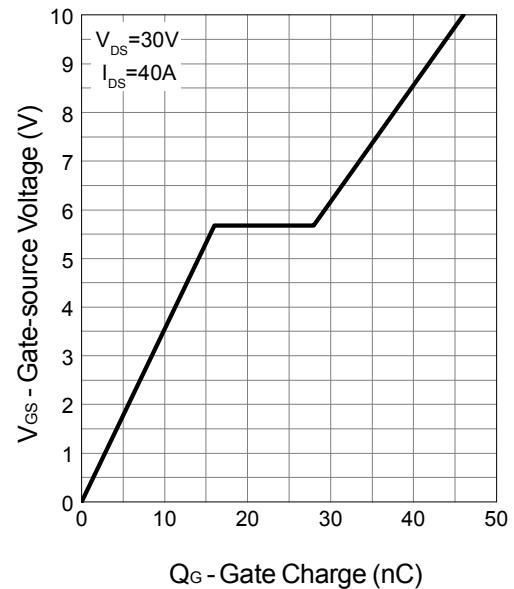
Typical Operating Characteristics



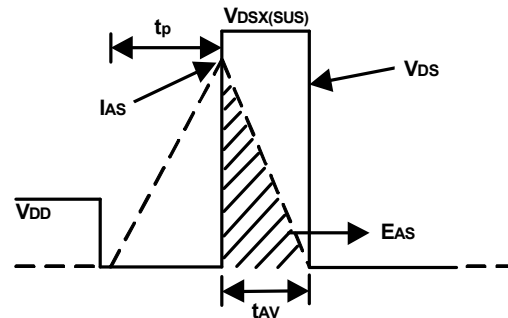
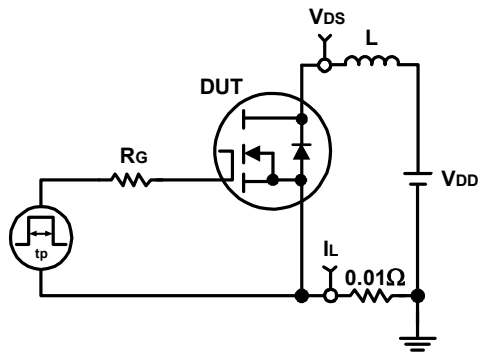
Typical Operating Characteristics (Cont.)



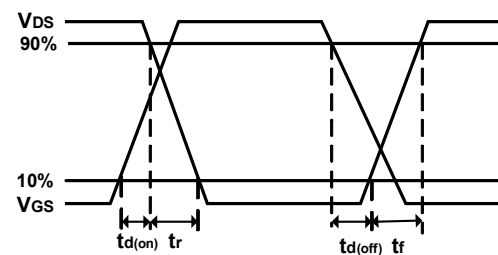
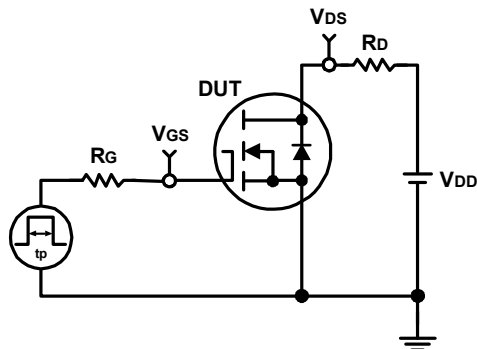
Typical Operating Characteristics (Cont.)

Drain-Source On Resistance

Source-Drain Diode Forward

Capacitance

Gate Charge


Avalanche Test Circuit and Waveforms

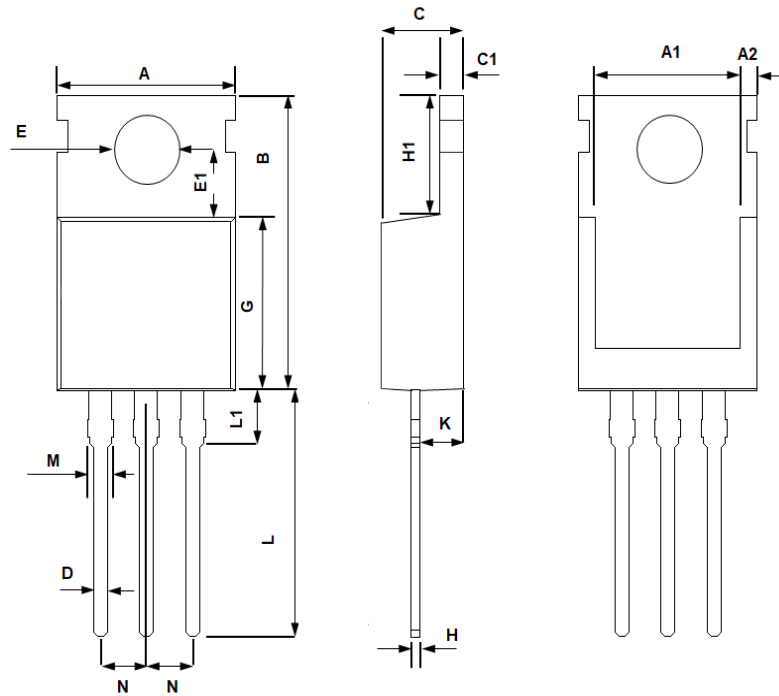


Switching Time Test Circuit and Waveforms



Package Information

TO-220



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	MAX	MIN	MAX	MIN
A	10.400	9.700	0.409	0.382
A1	8.900	7.400	0.350	0.291
A2	1.400	0.800	0.055	0.031
B	16.500	14.500	0.650	0.571
C	4.750	4.200	0.187	0.165
C1	1.500	1.100	0.059	0.043
D	1.000	0.600	0.039	0.024
E	4.000	3.300	0.157	0.130
E1	3.800	3.400	0.150	0.134
G	9.400	8.400	0.370	0.331
H	0.600	0.200	0.024	0.008
H1	6.850	6.200	0.270	0.244
K	2.850	2.100	0.112	0.083
L	14.000	12.500	0.551	0.492
L1	4.000	2.700	0.157	0.106
M	1.750	1.100	0.069	0.043
N	2.640	2.440	0.104	0.096